

## IN THE SPECIFICATION

Replace the partial paragraph beginning at page 16, line 1 with the following:  
steps will be described in detail herein below. An insulation layer 305, which may be alumina, is located between the write shield 304 and the write pole tip (PT) layer 132.

Replace the paragraph beginning at page 17, line 20 with the following replacement paragraph.

A non-magnetic sacrificial layer 140 such Ta or  $\text{Al}_2\text{O}_3$  is patterned by ion mill or reactive ion etching to form a write pole ~~sub tip~~ layer 132 and is preferably formed with a taper 135 at a pole tip region, which is toward the air bearing surface (ABS). A magnetic material is deposited on top of ~~write pole sub layer 132~~, the second pole piece layer 130 and planarized by chemical mechanical polishing (CMP) to expose the top surface of ~~write pole sub layer 132~~ non-magnetic sacrificial layer 140 (Ta or  $\text{Al}_2\text{O}_3$ ).

Replace the paragraph beginning at page 18, line 3 with the following replacement paragraph.

A write pole 138 is magnetically connected with the write pole ~~sub tip~~ layer 132. The write pole 138 is preferably formed of lamination layers of a high magnetic saturation material (high  $B_{sat}$ ) such as CoFe, NiFe, or their alloys with interspersed non-magnetic film such as Cr, Ru, etc.

Replace the paragraph beginning at page 18, line 10 with the following replacement paragraph.

Referring to Figs. 15A and 15B, reactive ion etching (RIE) is used to image transfer the image of the write pole 138 into the hard mask layer 203. Ion milling is subsequently used to image transfer the image of the write pole 138 into the lamination layers and define the x-direction of the write pole ~~sub tip~~ layer 132 and taper 135. The write pole 138 is formed with a trapezoidal shape to prevent adjacent track writing when the head experiences skew while flying over the disk. The layers of the write pole 138 are encapsulated by a non-magnetic material 206. The non-magnetic material 206 may be a RIEable material such as TaO<sub>x</sub>, SiO<sub>2</sub>, Si<sub>3</sub>N<sub>4</sub>, Ta, W, Al<sub>2</sub>O<sub>3</sub>, etc. The thickness of the non-magnetic layer 206 is at a level about equal to the beginning of the hard mask layer 203.